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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB1530

Silicon PNP Triple Diffused

RENESAS

ADE-208-879 (Z)
1st. Edition
September 2000

Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD2337

Outline

TO-220FM



1. Base
2. Collector
3. Emitter

Not recommended
for new design

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-200	V
Collector to emitter voltage	V_{CEO}	-150	V
Emitter to base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Collector peak current	$I_{C(peak)}$	-5	A
Collector power dissipation	P_C	1.5	W
	P_C^{*1}	20	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-45 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$.

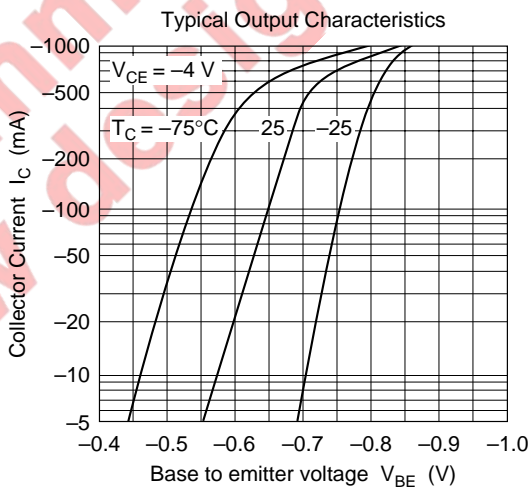
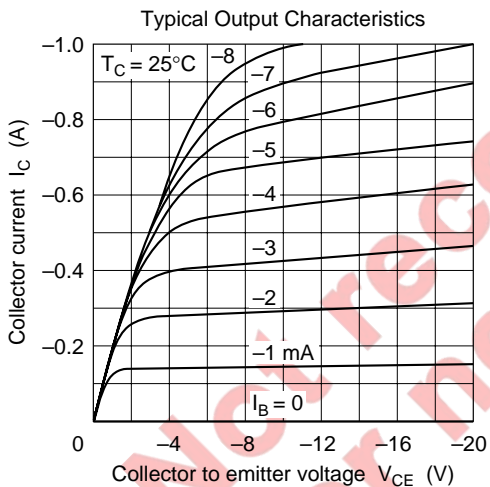
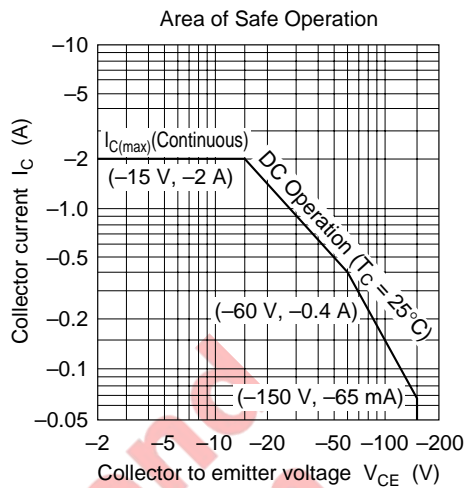
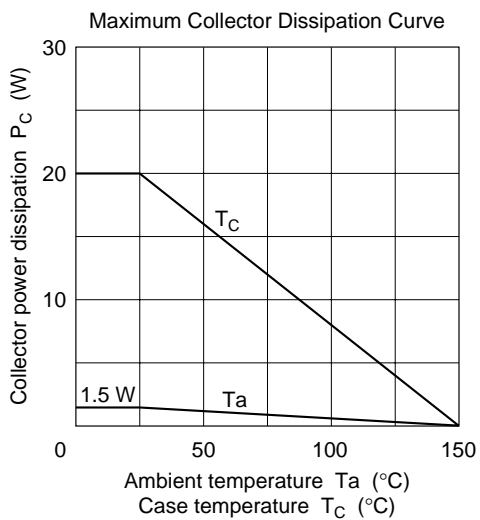
Electrical Characteristics (Ta = 25°C)

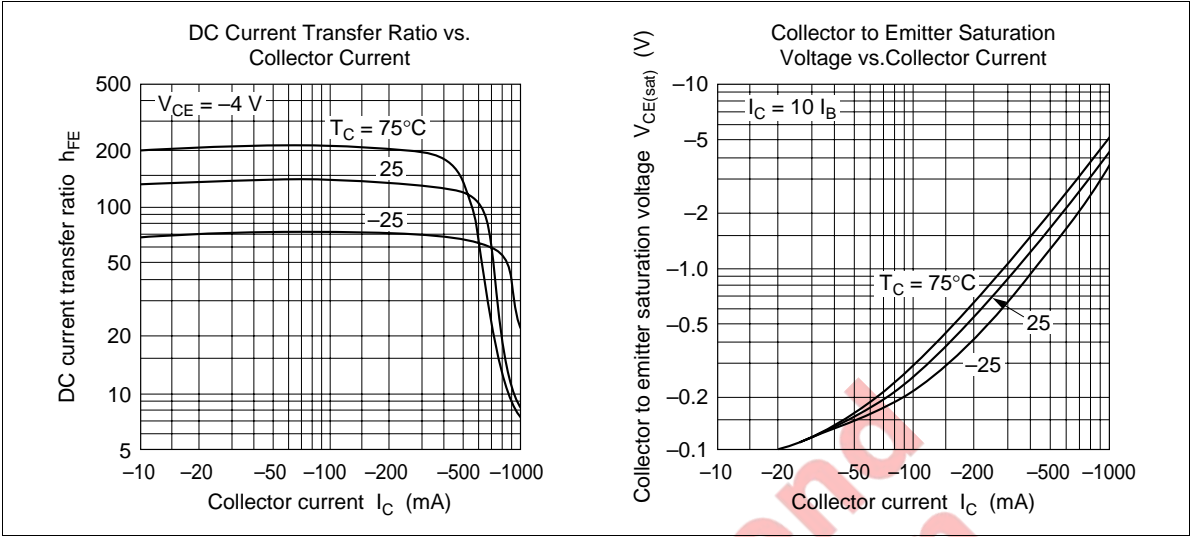
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-150	—	—	V	$I_C = -50\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -5\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	μA	$V_{CB} = -120\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = -4\text{ V}$, $I_C = -50\text{ mA}$
	h_{FE2}	60	—	—		$V_{CE} = -10\text{ V}$, $I_C = -500\text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-3	V	$I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-1	V	$I_{CE} = -4\text{ A}$, $I_C = -50\text{ mA}$

Notes: 1. The 2SB1530 is grouped by h_{FE1} as follows.

B	C
60 to 120	100 to 200

2. Pulse test.





Not recommended for new design

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